

Title (en)
SEMICONDUCTOR DIE HAVING A REDISTRIBUTION LAYER

Title (de)
HALBLEITERCHIP MIT EINER UMVERDRAHTUNGSSCHICHT

Title (fr)
DÉ SEMI-CONDUCTEUR DOTÉ D'UNE COUCHE DE REDISTRIBUTION

Publication
EP 2179442 A4 20130807 (EN)

Application
EP 08796037 A 20080627

Priority

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Abstract (en)
[origin: WO2009006284A2] A semiconductor device having a redistribution layer, and methods of forming same, are disclosed. After fabrication of semiconductor die on a wafer, a tape assembly is applied onto a surface of the wafer, in contact with the surfaces of each semiconductor die on the wafer. The tape assembly includes a backgrind tape as a base layer, and a film assembly adhered to the backgrind tape. The film assembly in turn includes an adhesive film on which is deposited a thin layer of conductive material. The redistribution layer pattern is traced into the tape assembly, using for example a laser. Thereafter, the unheated portions of the tape assembly may be removed, leaving the heated redistribution layer pattern on each semiconductor die.

IPC 8 full level
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